

FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10 μ A (Max.) @ $V_{DS} = -200V$
- Lower $R_{DS(ON)}$: 1.111 Ω (Typ.)

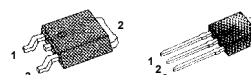
$$BV_{DSS} = -200 V$$

$$R_{DS(on)} = 1.5 \Omega$$

$$I_D = -3.1 A$$

D-PAK

I-PAK



1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	-200	V
I_D	Continuous Drain Current ($T_C=25^\circ C$)	-3.1	A
	Continuous Drain Current ($T_C=100^\circ C$)	-1.96	
I_{DM}	Drain Current-Pulsed ①	-12	A
V_{GS}	Gate-to-Source Voltage	+30	V
E_{AS}	Single Pulsed Avalanche Energy ②	256	mJ
I_{AR}	Avalanche Current ①	-3.1	A
E_{AR}	Repetitive Avalanche Energy ①	3.0	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
P_D	Total Power Dissipation ($T_A=25^\circ C$) *	2.5	W
	Total Power Dissipation ($T_C=25^\circ C$)	30	W
	Linear Derating Factor	0.24	W/ $^\circ C$
T_J, T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	4.17	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient *	--	50	
$R_{\theta JA}$	Junction-to-Ambient	--	110	

* When mounted on the minimum pad size recommended (PCB Mount).

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	-250	--	--	V	$V_{GS}=0V, I_D=-250\mu A$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	-0.22	--	$V/^{\circ}\text{C}$	$I_D=-250\mu A$ See Fig 7
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	--	-4.0	V	$V_{DS}=-5V, I_D=-250\mu A$
I_{GSS}	Gate-Source Leakage , Forward	--	--	-100	nA	$V_{GS}=-30V$
	Gate-Source Leakage , Reverse	--	--	100		$V_{GS}=30V$
I_{DSS}	Drain-to-Source Leakage Current	--	--	-10	μA	$V_{DS}=-250V$
		--	--	-100		$V_{DS}=-200V, T_C=125^{\circ}\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	1.3	Ω	$V_{GS}=-10V, I_D=-2.1A$ ④
g_{fs}	Forward Transconductance	--	3.0	--	S	$V_{DS}=-40V, I_D=-2.1A$ ④
C_{iss}	Input Capacitance	--	750	975	pF	$V_{GS}=0V, V_{DS}=-25V, f=1\text{MHz}$ See Fig 5
C_{oss}	Output Capacitance	--	110	165		
C_{rss}	Reverse Transfer Capacitance	--	45	65		
$t_{d(on)}$	Turn-On Delay Time	--	13	35	ns	$V_{DD}=-125V, I_D=-5.0A,$ $R_G=12\Omega$ See Fig 13 ④ ⑤
t_r	Rise Time	--	20	50		
$t_{d(off)}$	Turn-Off Delay Time	--	40	90		
t_f	Fall Time	--	16	40		
Q_g	Total Gate Charge	--	29	37	nC	$V_{DS}=-200V, V_{GS}=-10V,$ $I_D=-5.0A$ See Fig 6 & Fig 12 ④ ⑤
Q_{gs}	Gate-Source Charge	--	5.4	--		
Q_{gd}	Gate-Drain(" Miller ") Charge	--	15.5	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	-4.2	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	-17		
V_{SD}	Diode Forward Voltage ④	--	--	-5.0	V	$T_J=25^{\circ}\text{C}, I_S=-4.2A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	--	170	--	ns	$T_J=25^{\circ}\text{C}, I_F=-5.0A$
Q_{rr}	Reverse Recovery Charge	--	1.17	--	μC	$di_F/dt=100A/\mu s$ ④

Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
 ② $L=20\text{mH}, I_{AS}=-4.2A, V_{DD}=-50V, R_G=27\Omega^*,$ Starting $T_J=25^{\circ}\text{C}$
 ③ $I_{SD} \leq -5.0A, di/dt \leq 400A/\mu s, V_{DD} \leq BV_{DSS},$ Starting $T_J=25^{\circ}\text{C}$
 ④ Pulse Test : Pulse Width = $250\mu s,$ Duty Cycle $\leq 2\%$
 ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

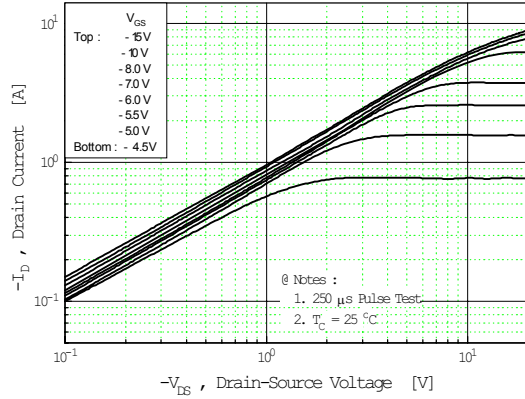


Fig 2. Transfer Characteristics

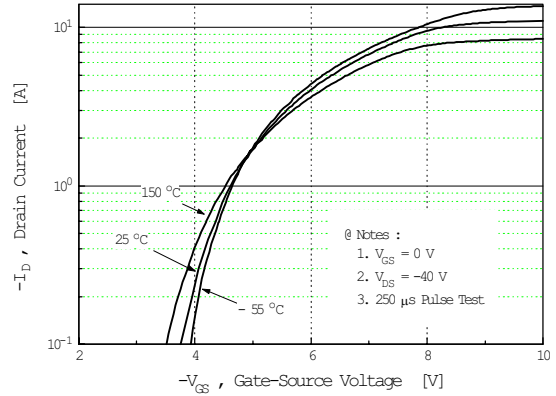


Fig 3. On-Resistance vs. Drain Current

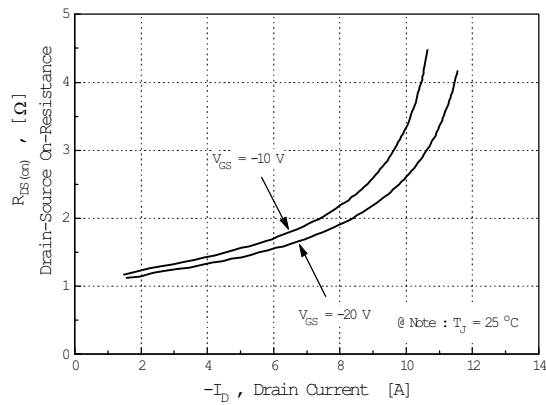


Fig 4. Source-Drain Diode Forward Voltage

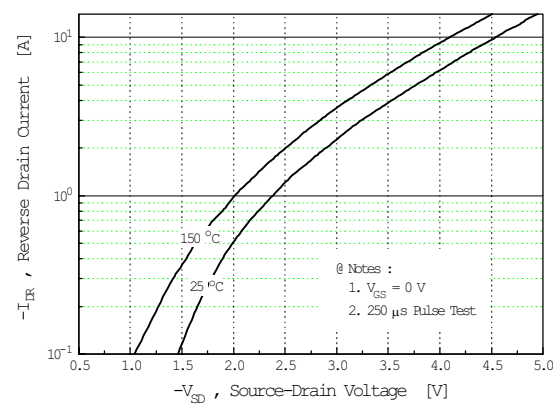


Fig 5. Capacitance vs. Drain-Source Voltage

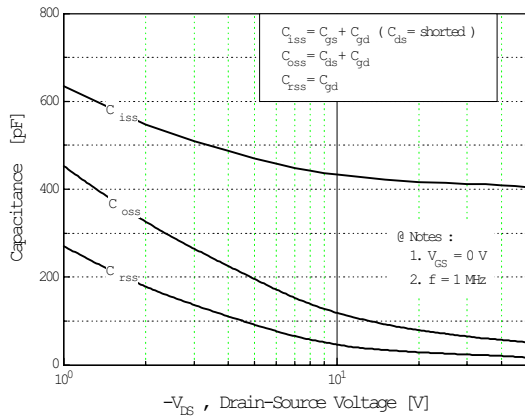


Fig 6. Gate Charge vs. Gate-Source Voltage

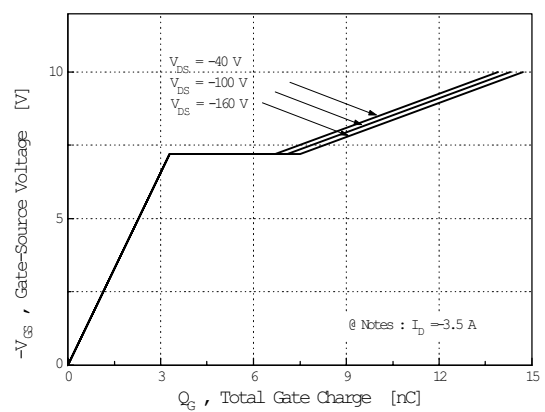


Fig 7. Breakdown Voltage vs. Temperature

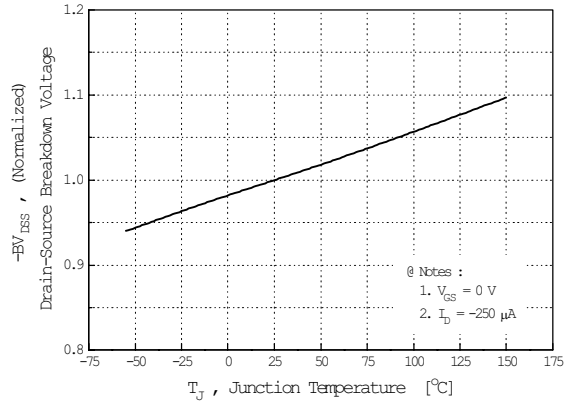


Fig 8. On-Resistance vs. Temperature

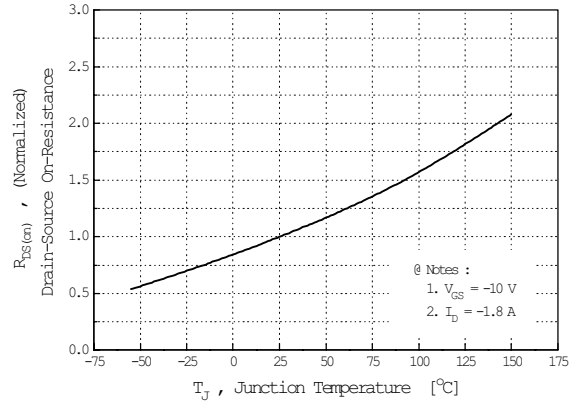


Fig 9. Max. Safe Operating Area

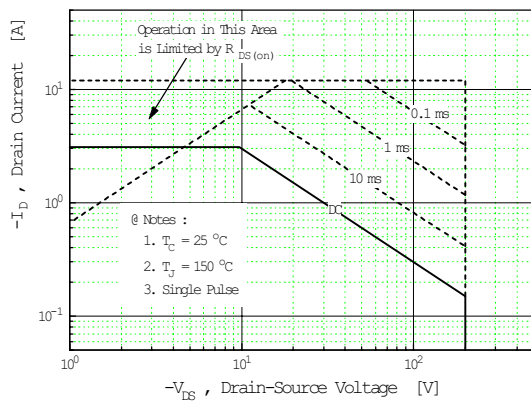


Fig 10. Max. Drain Current vs. Case Temperature

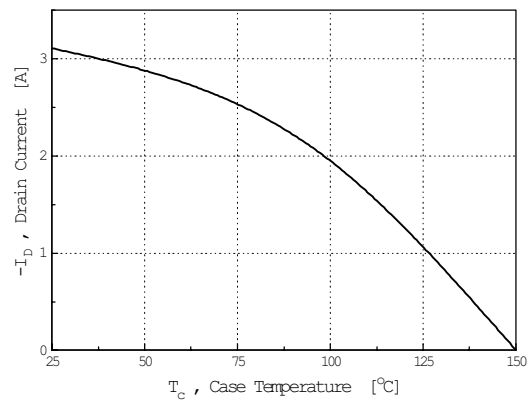


Fig 11. Thermal Response

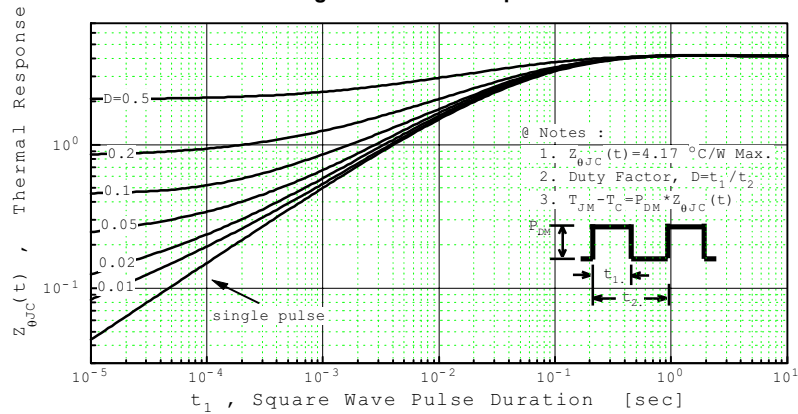


Fig 12. Gate Charge Test Circuit & Waveform

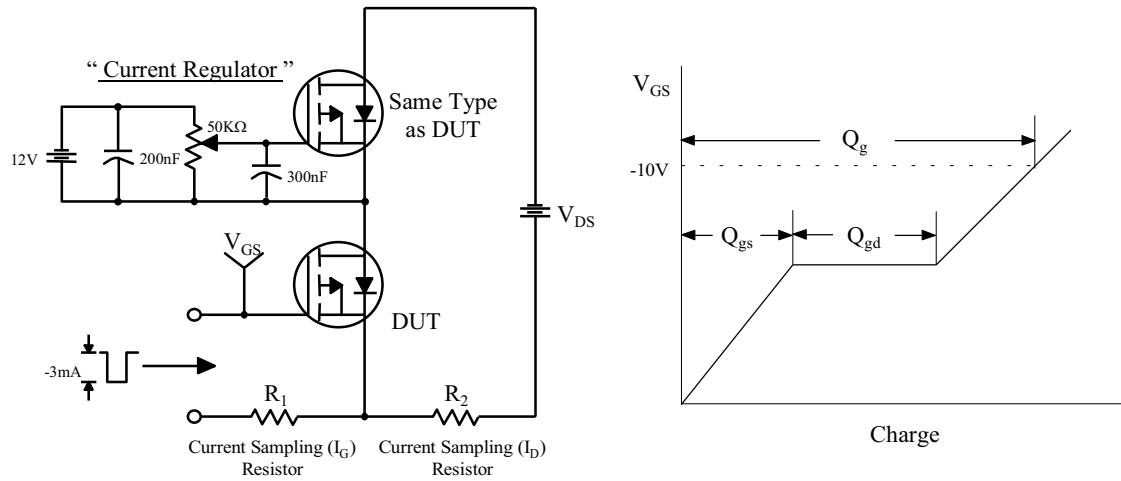


Fig 13. Resistive Switching Test Circuit & Waveforms

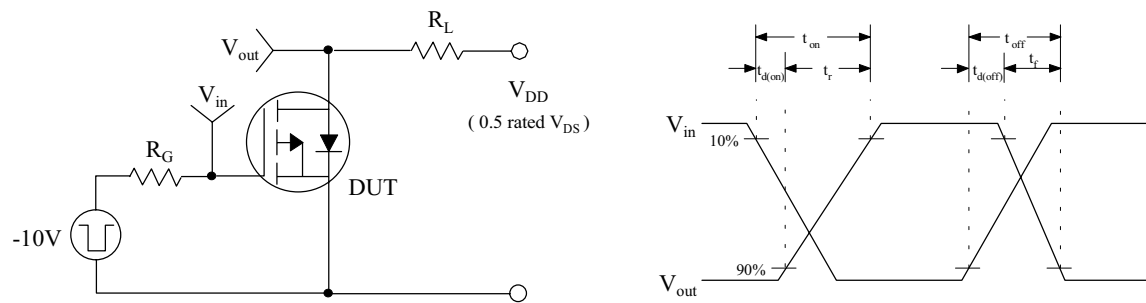


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

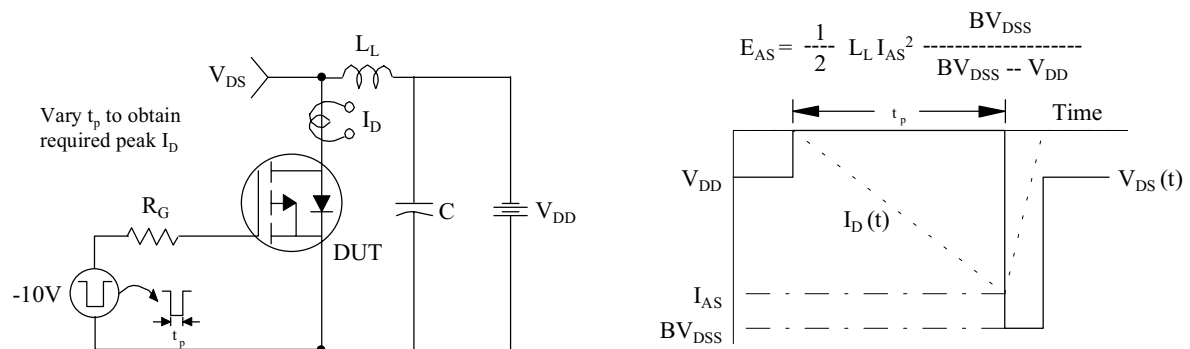


Diagram illustrating a switching circuit for a DUT (Device Under Test) using a Driver (N-Channel MOSFET).

The circuit includes a DUT, a Driver (N-Channel MOSFET), a load inductor L , and a DC source V_{DD} .

Key parameters and components shown:

- V_{DS} : Drain-Source Voltage across the DUT.
- I_S : Source current flowing through the DUT.
- V_{GS} : Gate-Source Voltage applied to the Driver.
- R_G : Gate resistor connected to the Driver.
- L : Load inductor.
- V_{DD} : DC supply voltage.

Operating conditions noted:

- dv/dt controlled by " R_G "
- I_S controlled by Duty Factor " D "

